

## 2SJ450

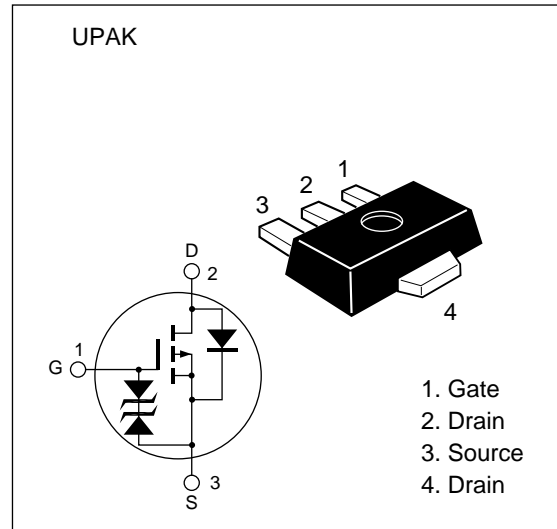
### Silicon P Channel MOS FET

#### Application

High speed power switching

#### Features

- Low on-resistance.
- Low drive power
- High speed switching
- 2.5V gate drive device.



**Table 1 Absolute Maximum Ratings** (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	-60	V
Gate to source voltage	$V_{GSS}$	±20	V
Drain current	$I_D$	-1	A
Drain peak current	$I_{D(pulse)^*}$	-2	A
Drain peak current	$I_{DR}$	-1	A
Channel dissipation	$P_{ch}^{**}$	1	W
Channel temperature	$T_{ch}$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

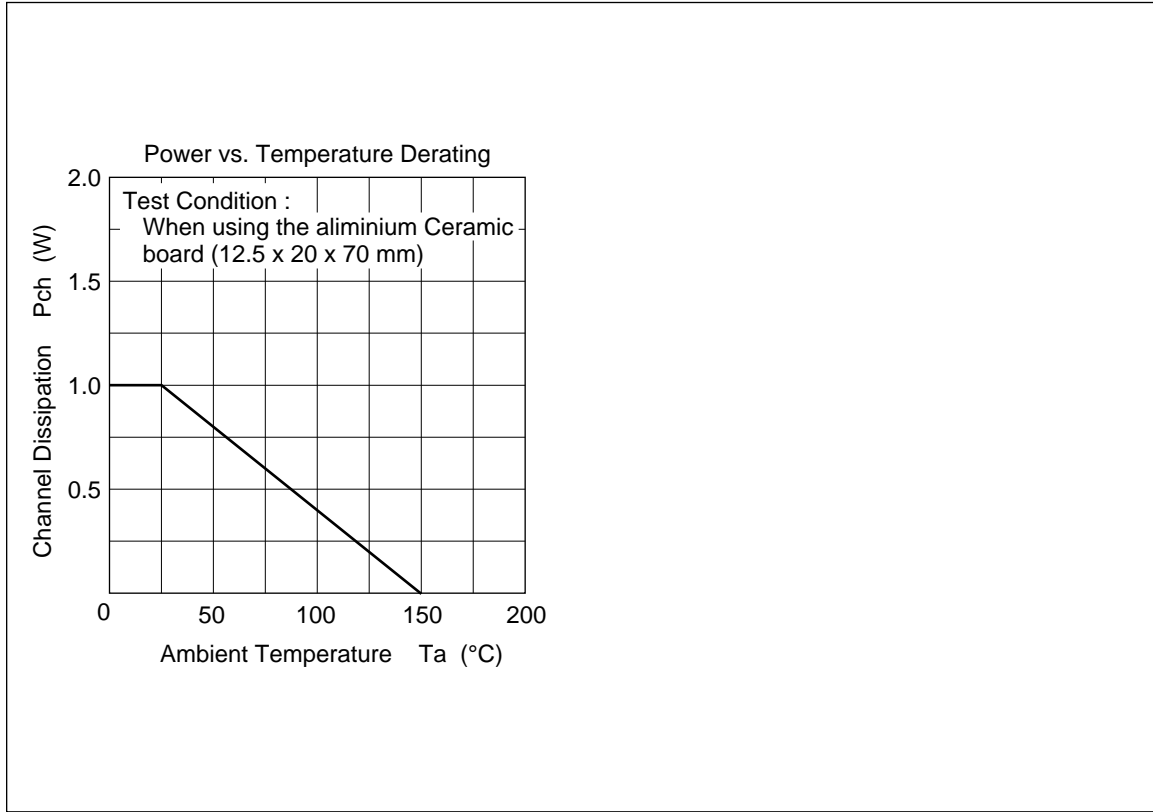
\*  $PW \leq 100 \mu s$ , duty cycle  $\leq 10 \%$

\*\* When using aluminium ceramic board (12.5 x 20 x 70 mm)

**Table 2 Electrical Characteristics (Ta = 25°C)**

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-60	—	—	V	$I_D = -10 \text{ mA}$ , $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	$\pm 20$	—	—	V	$I_G = \pm 100 \text{ }\mu\text{A}$ , $V_{DS} = 0$
Zero gate voltage drain current	$I_{DSS}$	—	—	-50	$\mu\text{A}$	$V_{DS} = -50 \text{ V}$ , $V_{GS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	$\pm 10$	$\mu\text{A}$	$V_{GS} = \pm 16 \text{ V}$ , $V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-0.5	—	-1.5	V	$V_{DS} = -10 \text{ V}$ , $I_D = -1 \text{ mA}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.85	1.2	$\Omega$	$I_D = -0.5 \text{ A}$ $V_{GS} = -4 \text{ V}^*$
Static drain to source on state resistance	$R_{DS(on)}$	—	1.1	1.9	$\Omega$	$I_D = -0.3 \text{ A}$ $V_{GS} = -2.5 \text{ V}^*$
Power transfer admittance	$ y_{fs} $	0.6	1.0	—	S	$I_D = -0.5 \text{ A}$ $V_{DS} = -10 \text{ V}$
Input capacitance	$C_{iss}$	—	150	—	pF	$V_{DS} = -10 \text{ V}$
Output capacitance	$C_{oss}$	—	72	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	$C_{rss}$	—	24	—	pF	$f = 1 \text{ MHz}$
Turn-on delay time	$t_{d(on)}$	—	6	—	$\mu\text{s}$	$V_{GS} = -10 \text{ V}$ , $I_D = -0.5 \text{ A}$
Rise time	$t_r$	—	9	—	$\mu\text{s}$	$R_L = 60 \text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	—	50	—	$\mu\text{s}$	
Fall time	$t_f$	—	35	—	$\mu\text{s}$	
Body-drain diode forward voltage	$V_{DF}$	—	-0.9	—	V	$I_F = -1 \text{ A}$ , $V_{GS} = 0$
Body-drain diode reverse recovery time	$t_{rr}$	—	100	—	ns	$I_F = -1 \text{ A}$ , $V_{GS} = 0$ $di_F / dt = 50 \text{ A} / \mu\text{s}$

\* Pulse Test  
Marking is "UY".



## Package Dimensions

Unit : mm

